

INTRALEVEL DECOUPLING CAPACITOR, METHOD OF MANUFACTURE AND TESTING CIRCUIT OF THE SAME

ABSTRACT OF THE DISCLOSURE

A decoupling capacitor is provided for a semiconductor device and may

5 include a first low dielectric insulator layer and a low resistance conductor formed
into at least two interdigitized patterns on the surface of the first low dielectric
insulator in a single interconnect plane. A high dielectric constant material may
be provided between the two patterns. A circuit for testing a plurality of these
capacitors is also provided which includes a charge monitoring circuit, a coupling
10 circuit and a control circuit.